

AMENDMENT TO THE SPECIFICATION

Please add the following new paragraph [0010a] after paragraph [0010] ending
5 on line 3 page 3:

--Fig. 4c is a schematic diagram of a Schottky diode clamped bipolar
junction transistor according to an alternate embodiment of the present
invention;

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Please replace paragraph [0037] beginning at page 12 line 21 with the following
rewritten paragraph:

-- [0037] Referring to ~~Fig. 4b~~Figs. 4b and 4c, an alternate embodiment
15 of the present invention is shown where electrical contact 416 is utilized to form
Schottky diode clamped bipolar junction transistor 402'. In this embodiment,
electrical contact 416 is formed from an electrically conductive layer wherein
electrical contact 416 forms Schottky barrier 414 to second polycrystalline
structure 446 and the electrically conductive layer further forms ohmic contact
20 412 to epitaxial structure 432. Such a Schottky diode clamped bipolar junction
transistor may also be formed, in still other embodiments, by utilizing the
electrically conductive layer to form an ohmic contact to a portion of epitaxial
semiconducting structure 432 and a Schottky barrier contact to a portion of first
polycrystalline structure 442.

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